

Ordering number:1787A

PNP/NPN Epitaxial Planar Silicon Transistors



2SB1121/2SD1621

High-Current Driver Applications

Applications

- Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- Adoption of FBET, MBIT processes.
- Low collector-to-emitter saturation voltage.
- Large current capacity and wide ASO.
- Fast switching speed.
- Very small size making it easy to provide high-density, small-sized hybrid IC's.

() : 2SB1121

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CB0}		(-30)	V
Collector-to-Emitter Voltage	V_{CEO}		(-25)	V
Emitter-to-Base Voltage	V_{EBO}		(-6)	V
Collector Current	I_C		(-2)	A
Collector Current (Pulse)	I_{CP}		(-5)	A
Collector Dissipation	P_C		500	mW
		Mounted on ceramic board (250mm ² ×0.8mm)	1.3	W
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)20V, I_E = 0$			(-0.1)	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-0.1)	μA
DC Current Gain	h_{FE1}	$V_{CE} = (-)2V, I_C = (-)100mA$	100*		560*	
	h_{FE2}	$V_{CE} = (-)2V, I_C = (-)1.5A$	65			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10V, I_C = (-)50mA$		150		MHz

* ; The 2SB1121/2SD1621 are classified by 100mA h_{FE} as follows :

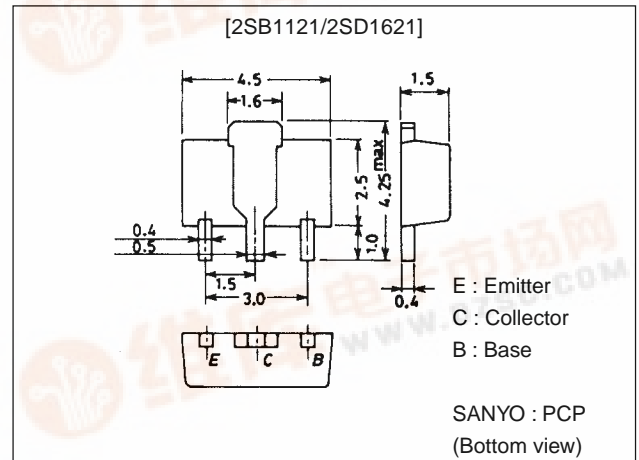
100	R	200	140	S	280	200	T	400	280	U	560
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Package Dimensions

unit:mm

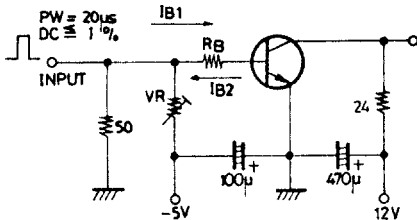
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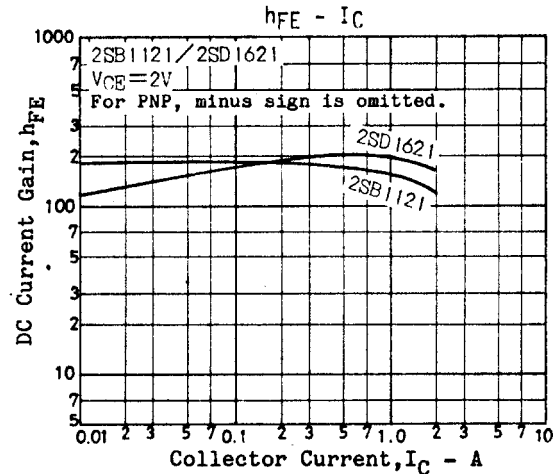
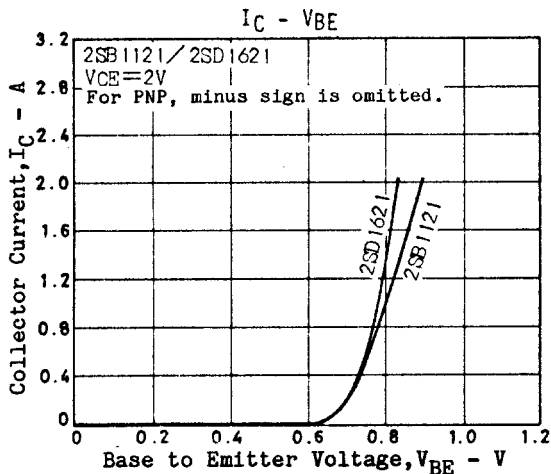
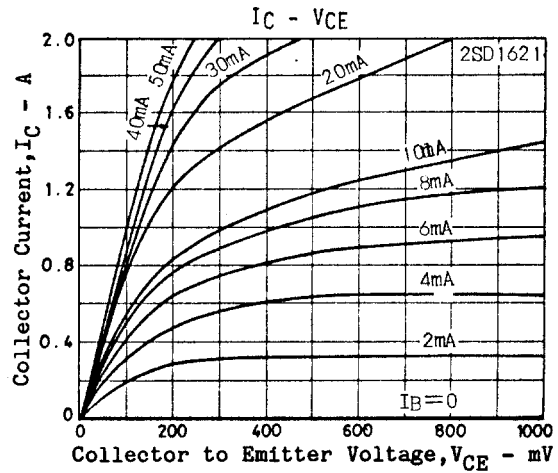
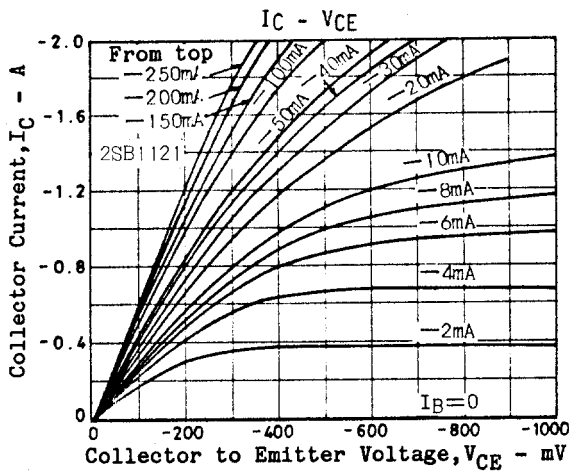
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA$		0.18	0.4	V
				(-0.35)	(-0.6)	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)1.5A, I_B=(-)75mA$		(-0.85)	(-1.2)	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-30)			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)1mA, R_{BE}=\infty$	(-25)			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu A, I_C=0$	(-6)			V
Output Capacitance	C_{ob}	$V_{CB}(-)10V, f=1MHz$		19		pF
				(32)		pF
Turn-ON Time	t_{on}	See specified Test Circuit.		60		ns
Storage Time	t_{stg}	See specified Test Circuit.		(60)		ns
				500		ns
Fall Time	t_f	See specified Test Circuit.		(350)		ns
				25		ns
				(25)		ns

Switching Time Test Circuit

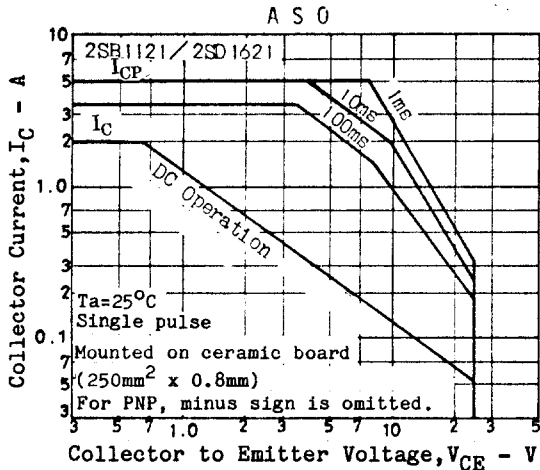
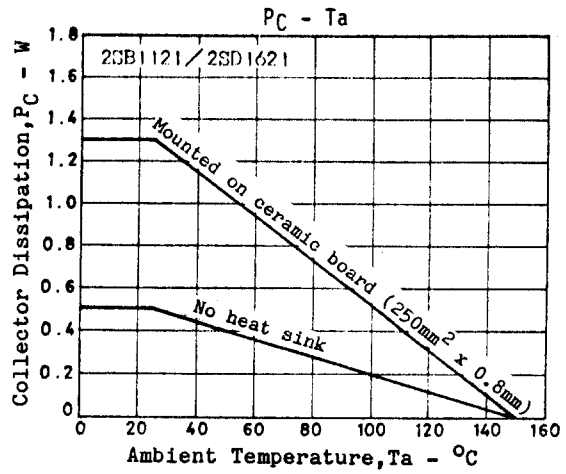
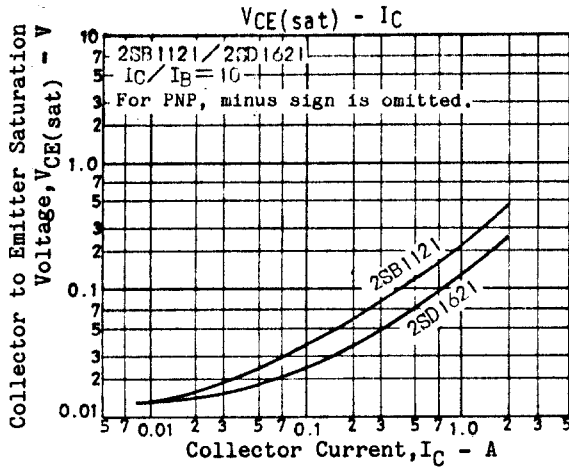
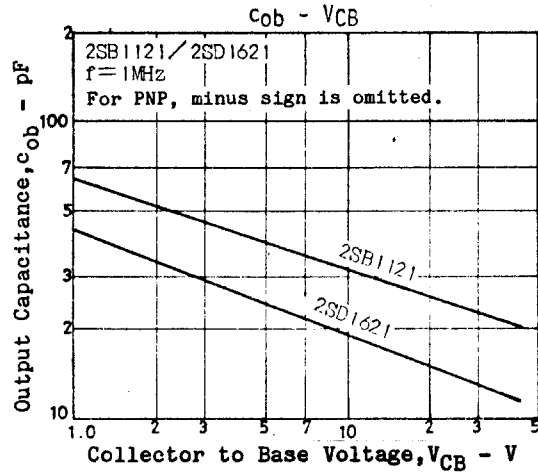
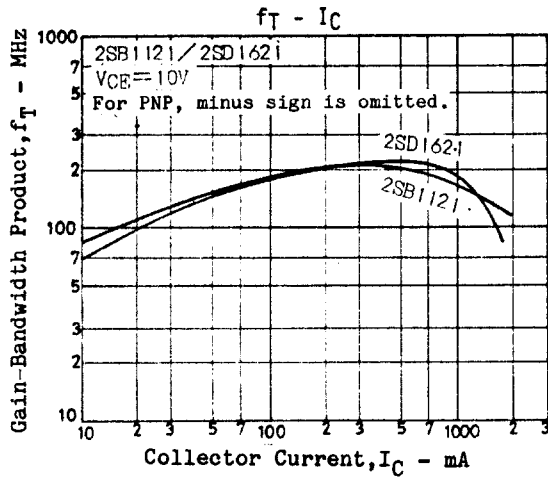


Marking 2SB1121:BD
2SD1621:DD
 h_{FE} rank :R,S,T,U

$20I_{B1} = -20I_{B2} = I_C = 500mA$
(For PNP, the polarity is reversed.)
Unit (resistance : Ω , capacitance : F)



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